

NCE60P50

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE60P50 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge .This device is well suited for high current load applications.

General Features

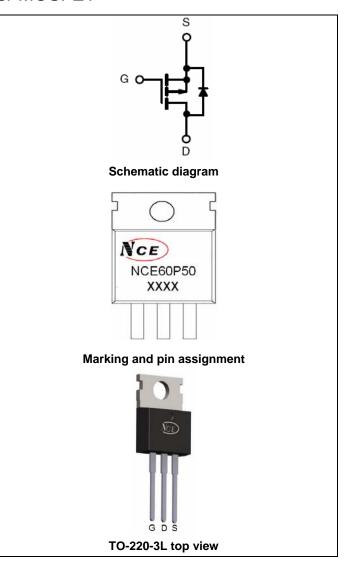
- V_{DS} =-60V, I_{D} =-50A $R_{DS(ON)}$ <28m Ω @ V_{GS} =-10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

Load switch

100% UIS TESTED!

100% AVds TESTED!



Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|----------|----------------|-----------|------------|----------|
| NCE60P50 | NCE60P50 | TO-220-3L | - | - | - |

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--------------------------------------------------|-----------------------|------------|-------------------------|
| Drain-Source Voltage | VDS | -60 | V |
| Gate-Source Voltage | Vgs | ±20 | V |
| Drain Current-Continuous | I _D | -50 | Α |
| Drain Current-Continuous(T _C =100 °C) | I _D (100℃) | -35 | А |
| Pulsed Drain Current | I _{DM} | -150 | А |
| Maximum Power Dissipation | P _D | 95 | W |
| Derating factor | | 0.76 | W/℃ |
| Single pulse avalanche energy (Note 5) | E _{AS} | 722 | mJ |
| Operating Junction and Storage Temperature Range | T_{J}, T_{STG} | -55 To 150 | $^{\circ}\! \mathbb{C}$ |



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Thermal Characteristic

| Thermal Resistance, Junction-to-Case ^(Note 2) | $R_{	heta JC}$ | 1.31 | °C/W | |
|----------------------------------------------------------|----------------|------|------|--|
|----------------------------------------------------------|----------------|------|------|--|

Electrical Characteristics (T_C=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|----------------------------------------------------------------------|-----|------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =-250μA | -60 | - | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =-60V,V _{GS} =0V - | | - | -1 | μΑ |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | • | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_{D}=-250\mu A$ | -2 | -2.6 | -3.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =-10V, I _D =-20A | - | 23 | 28 | mΩ |
| Forward Transconductance | g FS | V _{DS} =-10V,I _D =-20A | - | 25 | - | S |
| Dynamic Characteristics (Note4) | | | | 1 | | |
| Input Capacitance | C _{lss} |)/ OF)/)/ O)/ | - | 6460 | - | PF |
| Output Capacitance | Coss | V_{DS} =-25V, V_{GS} =0V, | - | 719 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | F=1.0MHz | - | 535 | - | PF |
| Switching Characteristics (Note 4) | | | | 1 | | |
| Turn-on Delay Time | t _{d(on)} | | - | 15 | - | nS |
| Turn-on Rise Time | t _r | V_{DD} =-30V, R_L =1.5 Ω , | - | 17 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | V_{GS} =-10 V , R_{G} =3 Ω | - | 40 | - | nS |
| Turn-Off Fall Time | t _f | | - | 45 | - | nS |
| Total Gate Charge | Qg | V 001 00A | - | 75 | | nC |
| Gate-Source Charge | Q_{gs} | V_{DS} =-30, I_{D} =-20A, | - | 16 | | nC |
| Gate-Drain Charge | Q_{gd} | V _{GS} =-10V | - | 19 | | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V,I _S =-20A | - | | -1.2 | V |
| Diode Forward Current (Note 2) | Is | | - | - | -20 | Α |
| Reverse Recovery Time | t _{rr} | TJ = 25°C, IF =- 20A | - | 50 | | nS |
| Reverse Recovery Charge | Qrr | di/dt = -100A/μs ^(Note3) | - | 59 | | nC |
| Forward Turn-On Time | t _{on} | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | |

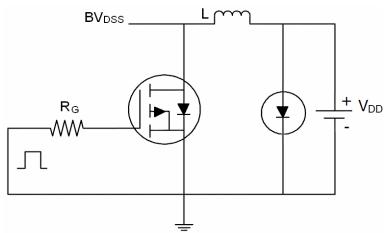
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition: Tj=25 $^{\circ}\text{C}$,V_{DD}=-20V,V_G=-10V,L=1mH,Rg=25 Ω ,I_{AS}=38A

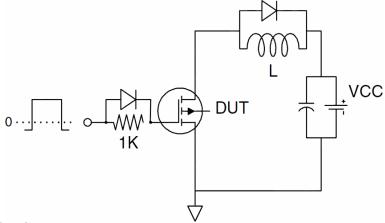


Test Circuit

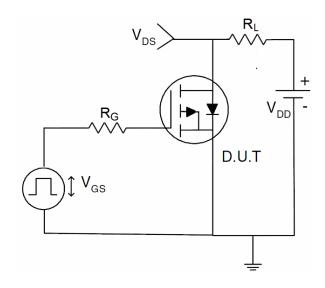
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



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Typical Electrical and Thermal Characteristics (Curves)

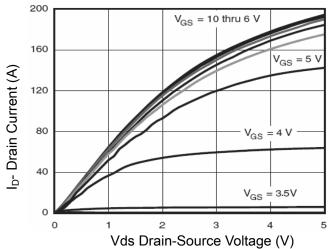


Figure 1 Output Characteristics

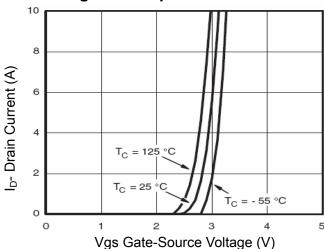


Figure 2 Transfer Characteristics

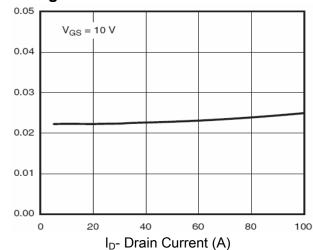


Figure 3 Rdson- Drain Current

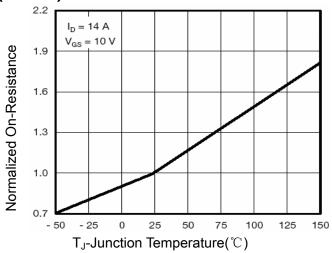


Figure 4 Rdson-Junction Temperature

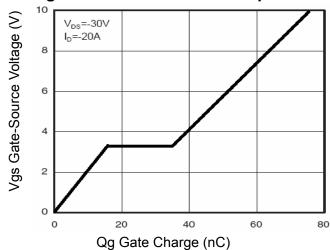


Figure 5 Gate Charge

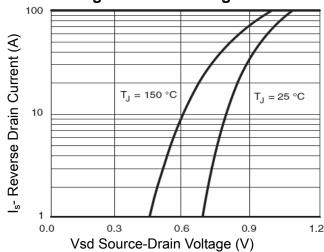


Figure 6 Source- Drain Diode Forward



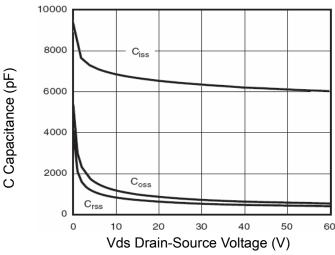


Figure 7 Capacitance vs Vds

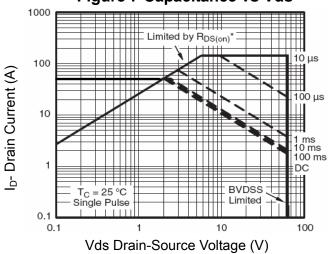


Figure 8 Safe Operation Area

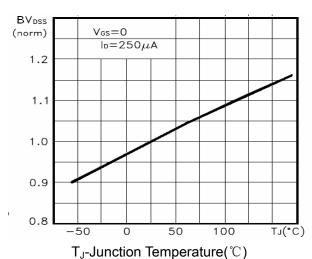


Figure 9 BV_{DSS} vs Junction Temperature

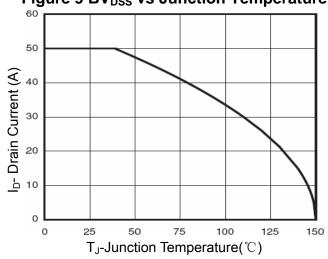


Figure 10 ID Current Derating vs Junction Temperature

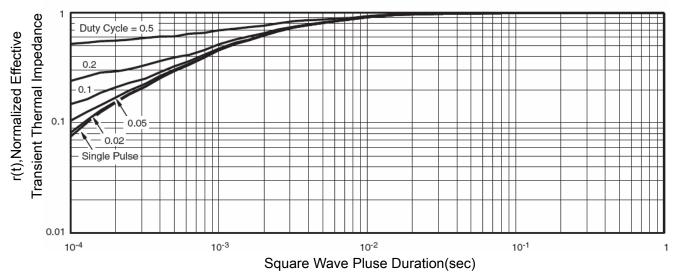


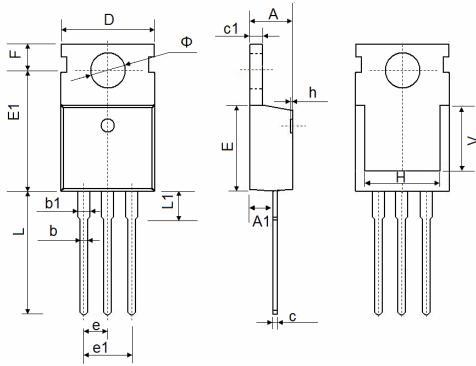
Figure 11 Normalized Maximum Transient Thermal Impedance

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NCE60P50

TO-220-3L Package Information



| Symbol | Dimensions | In Millimeters | Dimensions In Inches | | |
|--------|------------|----------------------|----------------------|-------|--|
| Symbol | Min. | Max. | Min. | Max. | |
| Α | 4.400 | 4.600 | 0.173 | 0.181 | |
| A1 | 2.250 | 2.550 | 0.089 | 0.100 | |
| b | 0.710 | 0.910 | 0.028 | 0.036 | |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 | |
| С | 0.330 | 0.650 | 0.013 | 0.026 | |
| c1 | 1.200 | 1.400 | 0.047 | 0.055 | |
| D | 9.910 | 10.250 | 0.390 | 0.404 | |
| Е | 8.9500 | 9.750 | 0.352 | 0.384 | |
| E1 | 12.650 | 12.950 | 0.498 | 0.510 | |
| е | 2.54 | 2.540 TYP. 0.100 TYP | | TYP. | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 | |
| F | 2.650 | 2.950 | 0.104 | 0.116 | |
| Н | 7.900 | 8.100 | 0.311 | 0.319 | |
| h | 0.000 | 0.300 | 0.000 | 0.012 | |
| L | 12.900 | 13.400 | 0.508 | 0.528 | |
| L1 | 2.850 | 3.250 | 0.112 | 0.128 | |
| V | 7.50 | 0 REF. | 0.295 REF. | | |
| Ф | 3.400 | 3.800 | 0.134 | 0.150 | |



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